TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5096

VHF~UHF Band Low Noise Amplifier Applications

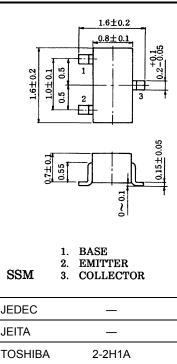
- Low noise figure, high gain.
- NF = 1.8dB, $|S_{21e}|^2 = 7.5$ dB (f = 2 GHz)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit | |
|-----------------------------|------------------|---------|------|--|
| Collector-base voltage | V _{CBO} | 20 | V | |
| Collector-emitter voltage | V _{CEO} | 10 | V | |
| Emitter-base voltage | V _{EBO} | 1.5 | V | |
| Base current | Ι _Β | 7 | mA | |
| Collector current | Ι _C | 15 | mA | |
| Collector power dissipation | PC | 100 | mW | |
| Junction temperature | Tj | 125 | °C | |
| Storage temperature range | T _{stg} | -55~125 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 2.4 mg (typ.)

Microwave Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|----------------------|-------------------------------------|---|-----|------|-----|------|--|
| Transition frequency | f _T | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 7 \text{ mA}$ | 7 | 10 | _ | GHz | |
| Insertion gain | S _{21e} ² (1) | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 1 \text{ GHz}$ | _ | 13 | _ | dB | |
| | S _{21e} ² (2) | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 7 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | 4.5 | 7.5 | _ | ub | |
| Noise figure | NF (1) | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 1 \text{ GHz}$ | _ | 1.4 | _ | dB | |
| | NF (2) | $V_{CE} = 6 \text{ V}, \text{ I}_{C} = 3 \text{ mA}, \text{ f} = 2 \text{ GHz}$ | _ | 1.8 | 3.0 | | |

Electrical Characteristics (Ta = 25°C)

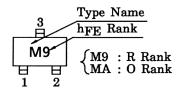
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------------|-----------------------------|--|-----|------|------|------|
| Collector cut-off current | I _{CBO} | $V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0$ | _ | | 1 | μA |
| Emitter cut-off current | I _{EBO} | $V_{EB} = 1 V, I_{C} = 0$ | _ | _ | 1 | μA |
| DC current gain | h _{FE} (Note 1) | $V_{CE} = 6 V, I_{C} = 7 mA$ | 50 | _ | 160 | |
| Output capacitance | C _{ob} | V _{CB} = 10 V, I _F = 0, f = 1 MHz (Note 2) | _ | 0.5 | _ | pF |
| Reverse transfer capacitance | C _{re} | $v_{CB} = 10 v, 1E = 0, 1 = 1 \text{ MHZ} (NOIE 2)$ | | 0.4 | 0.85 | pF |

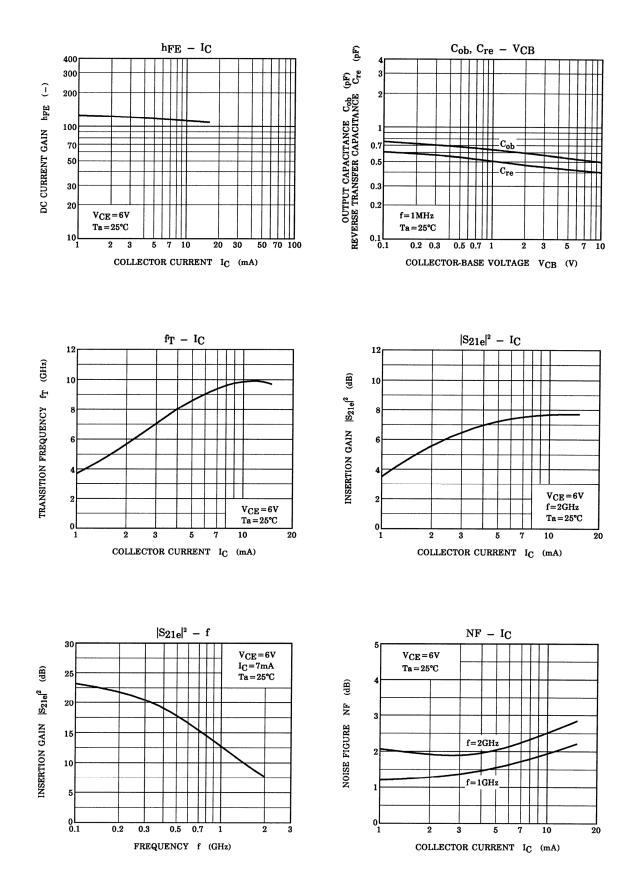
Note 1: hFE classification R: 50~100, O: 80~160

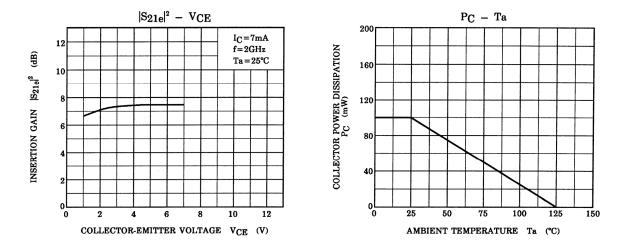
Note 2: Cre is measured by 3 terminal method with capacitance bridge.

Unit: mm

Marking







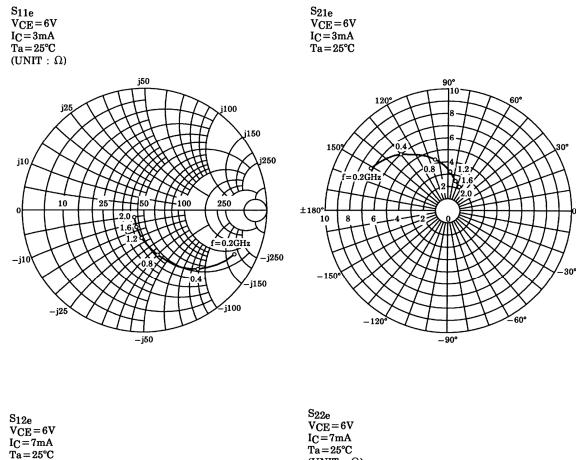
S-Parameter $Z_O = 50 \Omega$, Ta = 25°C

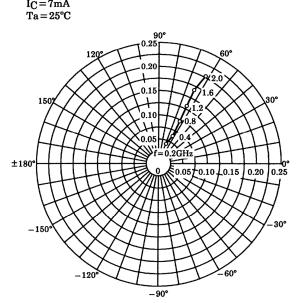
$V_{CE} = 6 V$, $I_C = 3 mA$

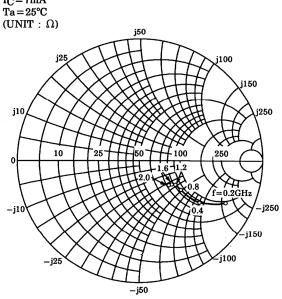
| Frequency | S11 | | S21 | | S12 | | S22 | |
|-----------|-------|--------|-------|-------|-------|------|-------|-------|
| (MHz) | Mag. | Ang. | Mag. | Ang. | Mag. | Ang. | Mag. | Ang. |
| 200 | 0.835 | -26.1 | 7.069 | 150.4 | 0.046 | 71.0 | 0.899 | -19.3 |
| 400 | 0.665 | -46.5 | 5.948 | 130.4 | 0.076 | 60.5 | 0.745 | -30.3 |
| 600 | 0.501 | -62.7 | 5.021 | 115.2 | 0.095 | 55.7 | 0.630 | -35.9 |
| 800 | 0.386 | -74.3 | 4.173 | 104.3 | 0.111 | 53.7 | 0.552 | -38.5 |
| 1000 | 0.297 | -83.7 | 3.592 | 95.6 | 0.124 | 53.2 | 0.500 | -39.9 |
| 1200 | 0.226 | -92.7 | 3.140 | 88.5 | 0.137 | 53.6 | 0.465 | -41.1 |
| 1400 | 0.175 | -101.9 | 2.808 | 82.3 | 0.152 | 54.1 | 0.442 | -42.2 |
| 1600 | 0.130 | -113.4 | 2.514 | 76.6 | 0.165 | 54.2 | 0.421 | -43.8 |
| 1800 | 0.103 | -128.0 | 2.293 | 71.7 | 0.179 | 53.9 | 0.405 | -45.7 |
| 2000 | 0.081 | -147.4 | 2.114 | 67.3 | 0.193 | 54.8 | 0.388 | -47.4 |

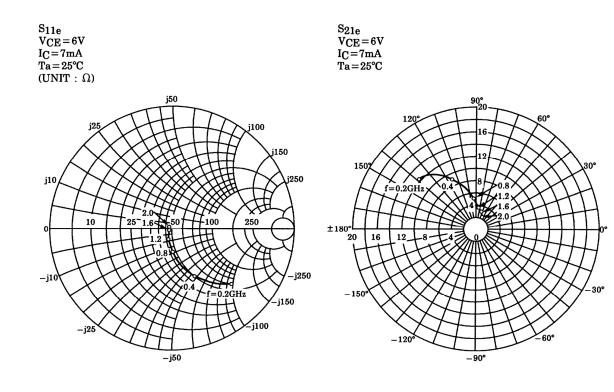
$V_{CE}=6\ V,\ I_C=7\ mA$

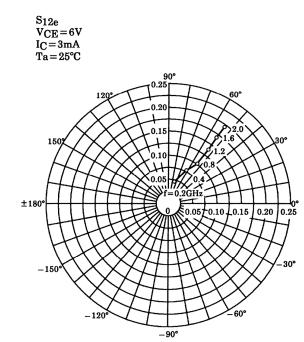
| Frequency | S11 | | S21 | | S12 | | S22 | |
|-----------|-------|--------|--------|-------|-------|------|-------|-------|
| (MHz) | Mag. | Ang. | Mag. | Ang. | Mag. | Ang. | Mag. | Ang. |
| 200 | 0.668 | -40.0 | 12.306 | 138.9 | 0.040 | 67.3 | 0.786 | -27.0 |
| 400 | 0.427 | -64.4 | 8.852 | 116.1 | 0.061 | 61.6 | 0.579 | -35.0 |
| 600 | 0.280 | -79.5 | 6.591 | 102.9 | 0.078 | 61.8 | 0.476 | -35.9 |
| 800 | 0.193 | -89.7 | 5.191 | 94.3 | 0.096 | 62.5 | 0.420 | -35.0 |
| 1000 | 0.134 | -99.3 | 4.288 | 87.8 | 0.112 | 63.2 | 0.390 | -34.2 |
| 1200 | 0.088 | -112.3 | 3.661 | 81.9 | 0.130 | 63.8 | 0.374 | -34.0 |
| 1400 | 0.056 | -129.8 | 3.232 | 76.9 | 0.150 | 63.4 | 0.366 | -34.8 |
| 1600 | 0.035 | -169.0 | 2.857 | 72.1 | 0.168 | 62.5 | 0.356 | -36.6 |
| 1800 | 0.040 | 157.0 | 2.574 | 68.1 | 0.185 | 61.4 | 0.347 | -39.0 |
| 2000 | 0.054 | 131.5 | 2.363 | 64.3 | 0.203 | 61.3 | 0.338 | -40.2 |



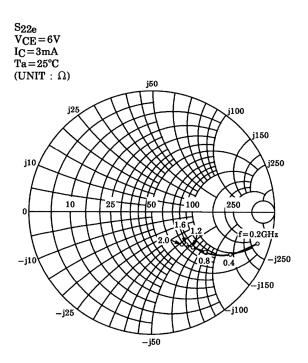








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